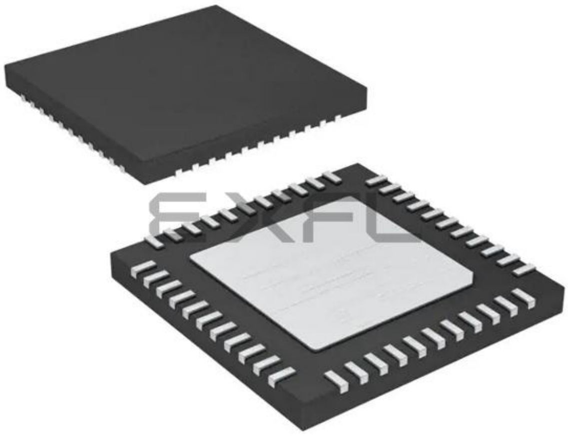

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	dsPIC
Core Size	16-Bit
Speed	20 MIPS
Connectivity	I²C, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	12
Program Memory Size	24KB (8K x 24)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	2.5V ~ 5.5V
Data Converters	A/D 8x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-VQFN Exposed Pad
Supplier Device Package	44-QFN (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/dspic30f3012t-20i-ml

2.2 Pins Used During Programming

The pins identified in Table 2-1 are used for device programming. Refer to the appropriate device data sheet for complete pin descriptions.

TABLE 2-1: dsPIC30F PIN DESCRIPTIONS DURING PROGRAMMING

Pin Name	Pin Type	Pin Description
$\overline{MCLR}$/VPP	P	Programming Enable
VDD	P	Power Supply
VSS	P	Ground
PGC	I	Serial Clock
PGD	I/O	Serial Data

Legend: I = Input, O = Output, P = Power

2.3 Program Memory Map

The program memory space extends from 0x0 to 0xFFFFFE. Code storage is located at the base of the memory map and supports up to 144 Kbytes (48K instruction words). Code is stored in three, 48 Kbyte memory panels that reside on-chip. Table 2-2 shows the location and program memory size of each device.

Locations 0x800000 through 0x8005BE are reserved for executive code memory. This region stores either the programming executive or debugging executive. The programming executive is used for device programming, while the debug executive is used for in-circuit debugging. This region of memory cannot be used to store user code.

Locations 0xF80000 through 0xF8000E are reserved for the Configuration registers. The bits in these registers may be set to select various device options, and are described in **Section 5.7 "Configuration Bits Programming"**.

Locations 0xFF0000 and 0xFF0002 are reserved for the Device ID registers. These bits can be used by the programmer to identify what device type is being programmed and are described in **Section 10.0 "Device ID"**. The device ID reads out normally, even after code protection is applied.

Figure 2-2 illustrates the memory map for the dsPIC30F devices.

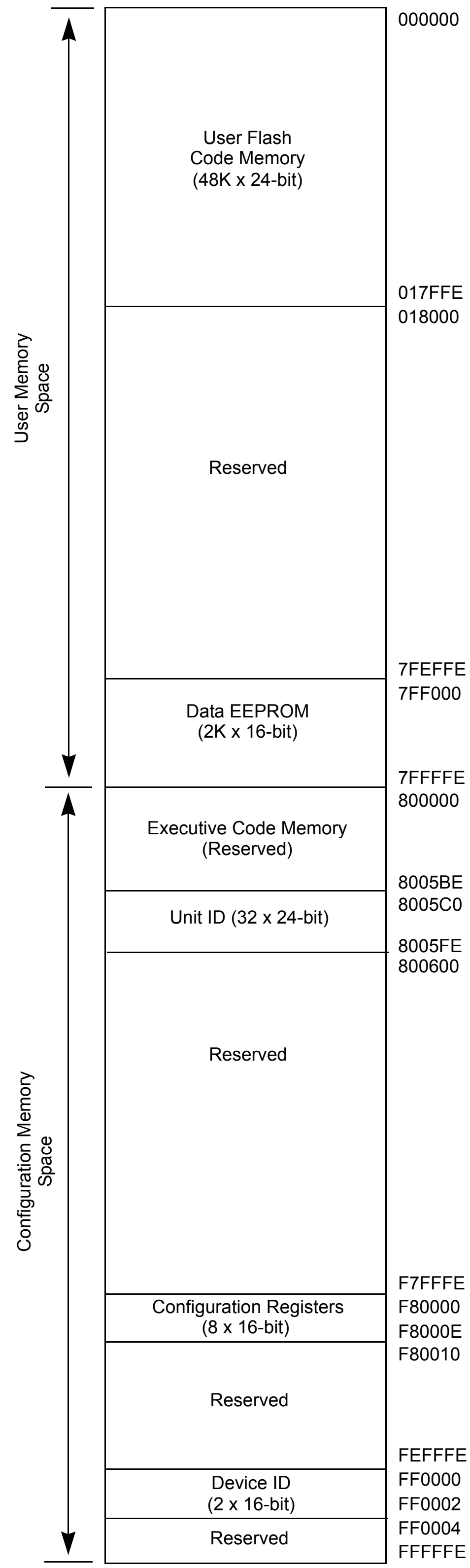
2.4 Data EEPROM Memory

The Data EEPROM array supports up to 4 Kbytes of data and is located in one memory panel. It is mapped in program memory space, residing at the end of User Memory Space (see Figure 2-2). Table 2-2 shows the location and size of data EEPROM in each device.

TABLE 2-2: CODE MEMORY AND DATA EEPROM MAP AND SIZE

Device	Code Memory map (Size in Instruction Words)	Data EEPROM Memory Map (Size in Bytes)
dsPIC30F2010	0x000000-0x001FFE (4K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F2011	0x000000-0x001FFE (4K)	None (0K)
dsPIC30F2012	0x000000-0x001FFE (4K)	None (0K)
dsPIC30F3010	0x000000-0x003FFE (8K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F3011	0x000000-0x003FFE (8K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F3012	0x000000-0x003FFE (8K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F3013	0x000000-0x003FFE (8K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F3014	0x000000-0x003FFE (8K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F4011	0x000000-0x007FFE (16K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F4012	0x000000-0x007FFE (16K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F4013	0x000000-0x007FFE (16K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F5011	0x000000-0x00AFFE (22K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F5013	0x000000-0x00AFFE (22K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F5015	0x000000-0x00AFFE (22K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F5016	0x000000-0x00AFFE (22K)	0x7FFC00-0x7FFFFE (1K)
dsPIC30F6010	0x000000-0x017FFE (48K)	0x7FF000-0x7FFFFE (4K)
dsPIC30F6010A	0x000000-0x017FFE (48K)	0x7FF000-0x7FFFFF (4K)
dsPIC30F6011	0x000000-0x015FFE (44K)	0x7FF800-0x7FFFFE (2K)
dsPIC30F6011A	0x000000-0x015FFE (44K)	0x7FF800-0x7FFFFE (2K)
dsPIC30F6012	0x000000-0x017FFE (48K)	0x7FF000-0x7FFFFE (4K)
dsPIC30F6012A	0x000000-0x017FFE (48K)	0x7FF000-0x7FFFFE (4K)
dsPIC30F6013	0x000000-0x015FFE (44K)	0x7FF800-0x7FFFFE (2K)
dsPIC30F6013A	0x000000-0x015FFE (44K)	0x7FF800-0x7FFFFE (2K)
dsPIC30F6014	0x000000-0x017FFE (48K)	0x7FF000-0x7FFFFE (4K)
dsPIC30F6014A	0x000000-0x017FFE (48K)	0x7FF000-0x7FFFFE (4K)
dsPIC30F6015	0x000000-0x017FFE (48K)	0x7FF000-0x7FFFFE (4K)

FIGURE 2-2: PROGRAM MEMORY MAP



Note: The address boundaries for user Flash code memory and data EEPROM are device-dependent.

5.0 DEVICE PROGRAMMING

5.1 Overview of the Programming Process

Once the programming executive has been verified in memory (or loaded if not present), the dsPIC30F can be programmed using the command set shown in Table 5-1. A detailed description for each command is provided in **Section 8.0 "Programming Executive Commands"**.

TABLE 5-1: COMMAND SET SUMMARY

Command	Description
`SCHECK`	Sanity check
`READD`	Read data EEPROM, Configuration registers and device ID
`READP`	Read code memory
`PROGD`	Program one row of data EEPROM and verify
`PROGP`	Program one row of code memory and verify
`PROGC`	Program Configuration bits and verify
`ERASEB`	Bulk Erase, or erase by segment
`ERASED`	Erase data EEPROM
`ERASEP`	Erase code memory
`QBLANK`	Query if the code memory and data EEPROM are blank
`QVER`	Query the software version

A high-level overview of the programming process is illustrated in Figure 5-1. The process begins by entering Enhanced ICSP mode. The chip is then bulk erased, which clears all memory to '1' and allows the device to be programmed. The Chip Erase is verified before programming begins. Next, the code memory, data Flash and Configuration bits are programmed. As these memories are programmed, they are each verified to ensure that programming was successful. If no errors are detected, the programming is complete and Enhanced ICSP mode is exited. If any of the verifications fail, the procedure should be repeated, starting from the Chip Erase.

If Advanced Security features are enabled, then individual Segment Erase operations need to be performed, based on user selections (i.e., based on the specific needs of the user application). The specific operations that are used typically depend on the order in which various segments need to be programmed for a given application or system.

Section 5.2 "Entering Enhanced ICSP Mode" through **Section 5.8 "Exiting Enhanced ICSP Mode"** describe the programming process in detail.

FIGURE 5-1: PROGRAMMING FLOW

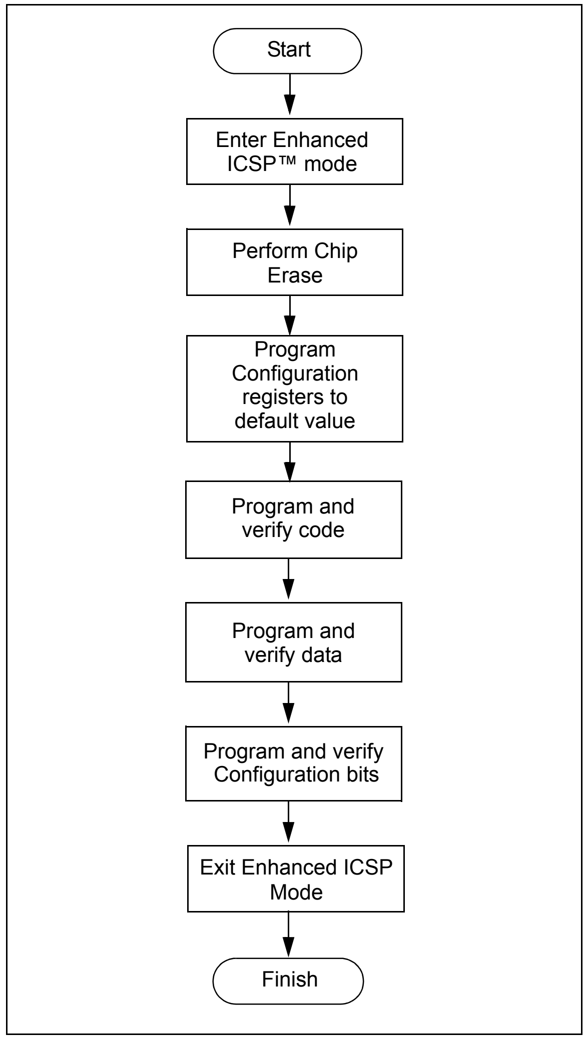


TABLE 5-7: CONFIGURATION BITS DESCRIPTION (CONTINUED)

Bit Field	Register	Description
EBS	FBS	**Boot Segment Data EEPROM Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)** 1 = No Data EEPROM is reserved for Boot Segment 0 = 128 bytes of Data EEPROM are reserved for Boot Segment in dsPIC30F5011/5013, and 256 bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015
BSS<2:0>	FBS	**Boot Segment Program Memory Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)** 111 = No Boot Segment 110 = Standard security; Small-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x0003FF] 101 = Standard security; Medium-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x000FFF] 100 = Standard security; Large-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x001FF] 011 = No Boot Segment 010 = High security; Small-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x0003FF] 001 = High security; Medium-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x000FFF] 000 = High security; Large-sized Boot Program Flash [Boot Segment starts after BS and ends at 0x001FFF]
BWRP	FBS	**Boot Segment Program Memory Write Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)** 1 = Boot Segment program memory is not write-protected 0 = Boot Segment program memory is write-protected
RSS<1:0>	FSS	**Secure Segment Data RAM Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)** 11 = No Data RAM is reserved for Secure Segment 10 = Small-sized Secure RAM [(256 – N) bytes of RAM are reserved for Secure Segment] 01 = Medium-sized Secure RAM [(768 – N) bytes of RAM are reserved for Secure Segment in dsPIC30F5011/5013, and (2048 – N) bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015] 00 = Large-sized Secure RAM [(1024 – N) bytes of RAM are reserved for Secure Segment in dsPIC30F5011/5013, and (4096 – N) bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015] where N = Number of bytes of RAM reserved for Boot Sector.
ESS<1:0>	FSS	**Secure Segment Data EEPROM Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)** 11 = No Data EEPROM is reserved for Secure Segment 10 = Small-sized Secure Data EEPROM [(128 – N) bytes of Data EEPROM are reserved for Secure Segment in dsPIC30F5011/5013, and (256 – N) bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015] 01 = Medium-sized Secure Data EEPROM [(256 – N) bytes of Data EEPROM are reserved for Secure Segment in dsPIC30F5011/5013, and (512 – N) bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015] 00 = Large-sized Secure Data EEPROM [(512 – N) bytes of Data EEPROM are reserved for Secure Segment in dsPIC30F5011/5013, (1024 – N) bytes in dsPIC30F6011A/6013A, and (2048 – N) bytes in dsPIC30F6010A/6012A/6014A/6015] where N = Number of bytes of Data EEPROM reserved for Boot Sector.

TABLE 5-8: dsPIC30F CONFIGURATION REGISTERS (FOR dsPIC30F2010, dsPIC30F4011/4012 AND dsPIC30F6010/ 6011/6012/6013/ 6014)

Address	Name	Bit 15	Bit 14	Bit 13	Bit 12	Bit 11	Bit 10	Bit 9	Bit 8	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
0xF80000	FOSC	FCKSM<1:0>		—	—	—	—	FOS<1:0>		—	—	—	—	FPR<3:0>			
0xF80002	FWDT	FWDTEN	—	—	—	—	—	—	—	—	—	FWPSA<1:0>		FWPSB<3:0>			
0xF80004	FBORPOR	MCLREN	—	—	—	—	PWMPIN(1)	HPOL(1)	LPOL(1)	BOREN	—	BORV<1:0>		—	—	FPWRT<1:0>	
0xF80006	FBS	—	—	Reserved(2)		—	—	—	Reserved(2)	—	—	—	—	Reserved(2)			
0xF80008	FSS	—	—	Reserved(2)		—	—	Reserved(2)		—	—	—	—	Reserved(2)			
0xF8000A	FGS	—	—	—	—	—	—	—	—	—	—	—	—	—	Reserved(2)	GCP	GWRP
0xF8000C	FICD	BKBUG	COE	—	—	—	—	—	—	—	—	—	—	—	—	ICS<1:0>	

Note 1: On the 6011, 6012, 6013 and 6014, these bits are reserved (read as '1' and must be programmed as '1').
2: Reserved bits read as '1' and must be programmed as '1'.

TABLE 5-9: dsPIC30F CONFIGURATION REGISTERS (FOR dsPIC30F5011/5013)

Address	Name	Bit 15	Bit 14	Bit 13	Bit 12	Bit 11	Bit 10	Bit 9	Bit 8	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
0xF80000	FOSC	FCKSM<1:0>		—	—	—	—	FOS<1:0>		—	—	—	—	FPR<3:0>			
0xF80002	FWDT	FWDTEN	—	—	—	—	—	—	—	—	—	FWPSA<1:0>		FWPSB<3:0>			
0xF80004	FBORPOR	MCLREN	—	—	—	—	Reserved(1)			BOREN	—	BORV<1:0>		—	—	FPWRT<1:0>	
0xF80006	FBS	—	—	RBS<1:0>		—	—	—	EBS	—	—	—	—	BSS<2:0>			BWRP
0xF80008	FSS	—	—	RSS<1:0>		—	—	ESS<1:0>		—	—	—	—	SSS<2:0>			SWRP
0xF8000A	FGS	—	—	—	—	—	—	—	—	—	—	—	—	—	GSS<1:0>		GWRP
0xF8000C	FICD	BKBUG	COE	—	—	—	—	—	—	—	—	—	—	—	—	ICS<1:0>	

Note 1: Reserved bits read as '1' and must be programmed as '1'.

6.0 OTHER PROGRAMMING FEATURES

6.1 Erasing Memory

Memory is erased by using an ERASEB, ERASED or ERASEP command, as detailed in **Section 8.5 "Command Descriptions"**. Code memory can be erased by row using ERASEP. Data EEPROM can be erased by row using ERASED. When memory is erased, the affected memory locations are set to '1's.

ERASEB provides several Bulk Erase options. Performing a Chip Erase with the ERASEB command clears all code memory, data EEPROM and code protection registers. Alternatively, ERASEB can be used to selectively erase either all code memory or data EEPROM. Erase options are summarized in Table 6-1.

TABLE 6-1: ERASE OPTIONS

Command	Affected Region
ERASEB	Entire chip(1) or all code memory or all data EEPROM, or erase by segment
ERASED	Specified rows of data EEPROM
ERASEP(2)	Specified rows of code memory

Note 1: The system operation Configuration registers and device ID registers are not erasable.

2: ERASEP cannot be used to erase code-protect Configuration bits. These bits must be erased using ERASEB.

6.2 Modifying Memory

Instead of bulk-erasing the device before programming, it is possible that you may want to modify only a section of an already programmed device. In this situation, Chip Erase is not a realistic option.

Instead, you can erase selective rows of code memory and data EEPROM using ERASEP and ERASED, respectively. You can then reprogram the modified rows with the PROGP and PROGD command pairs. In these cases, when code memory is programmed, single-panel programming must be specified in the PROGP command.

For modification of Advanced Code Protection bits for a particular segment, the entire chip must first be erased with the ERASEB command. Alternatively, on devices that support Advanced Security, individual segments (code and/or data EEPROM) may be erased, by suitably changing the MS (Memory Select) field in the ERASEB command. The code-protect Configuration bits can then be reprogrammed using the PROGC command.

Note: If read or write code protection is enabled for a segment, no modifications can be made to that segment until code protection is disabled. Code protection can only be disabled by performing a Chip Erase or by performing a Segment Erase operation for the required segment.

6.3 Reading Memory

The READD command reads the data EEPROM, Configuration bits and device ID of the device. This command only returns 16-bit data and operates on 16-bit registers. READD can be used to return the entire contents of data EEPROM.

The READP command reads the code memory of the device. This command only returns 24-bit data packed as described in **Section 8.3 "Packed Data Format"**. READP can be used to read up to 32K instruction words of code memory.

Note: Reading an unimplemented memory location causes the programming executive to reset. All READD and READP commands **must** specify only valid memory locations.

6.4 Programming Executive Software Version

At times, it may be necessary to determine the version of programming executive stored in executive memory. The QVER command performs this function. See **Section 8.5.11 "QVER Command"** for more details about this command.

6.5 Data EEPROM Information in the Hexadecimal File

To allow portability of code, the programmer must read the data EEPROM information from the hexadecimal file. If data EEPROM information is not present, a simple warning message should be issued by the programmer. Similarly, when saving a hexadecimal file, all data EEPROM information must be included. An option to not include the data EEPROM information can be provided.

Microchip Technology Inc. believes that this feature is important for the benefit of the end customer.

6.6 Configuration Information in the Hexadecimal File

To allow portability of code, the programmer must read the Configuration register locations from the hexadecimal file. If configuration information is not present in the hexadecimal file, a simple warning message should be issued by the programmer. Similarly, while saving a hexadecimal file, all configuration information must be included. An option to not include the configuration information can be provided.

Microchip Technology Inc. feels strongly that this feature is important for the benefit of the end customer.

6.7 Unit ID

The dsPIC30F devices contain 32 instructions of Unit ID. These are located at addresses 0x8005C0 through 0x8005FF. The Unit ID can be used for storing product information such as serial numbers, system manufacturing dates, manufacturing lot numbers and other such application-specific information.

A Bulk Erase does not erase the Unit ID locations. Instead, erase all executive memory using steps 1-4 as shown in Table 12-1, and program the Unit ID along with the programming executive. Alternately, use a Row Erase to erase the row containing the Unit ID locations.

6.8 Checksum Computation

Checksums for the dsPIC30F are 16 bits in size. The checksum is to total sum of the following:

- Contents of code memory locations
- Contents of Configuration registers

Table A-1 describes how to calculate the checksum for each device. All memory locations are summed one byte at a time, using only their native data size. More specifically, Configuration and device ID registers are summed by adding the lower two bytes of these locations (the upper byte is ignored), while code memory is summed by adding all three bytes of code memory.

Note:	The checksum calculation differs depending on the code-protect setting. Table A-1 describes how to compute the checksum for an unprotected device and a read-protected device. Regardless of the code-protect setting, the Configuration registers can always be read.

7.0 PROGRAMMER – PROGRAMMING EXECUTIVE COMMUNICATION

7.1 Communication Overview

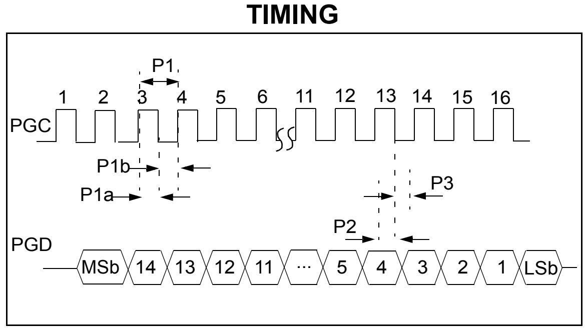
The programmer and programming executive have a master-slave relationship, where the programmer is the master programming device and the programming executive is the slave.

All communication is initiated by the programmer in the form of a command. Only one command at a time can be sent to the programming executive. In turn, the programming executive only sends one response to the programmer after receiving and processing a command. The programming executive command set is described in **Section 8.0 “Programming Executive Commands”**. The response set is described in **Section 9.0 “Programming Executive Responses”**.

7.2 Communication Interface and Protocol

The Enhanced ICSP interface is a 2-wire SPI interface implemented using the PGC and PGD pins. The PGC pin is used as a clock input pin, and the clock source must be provided by the programmer. The PGD pin is used for sending command data to, and receiving response data from, the programming executive. All serial data is transmitted on the falling edge of PGC and latched on the rising edge of PGC. All data transmissions are sent Most Significant bit (MSb) first, using 16-bit mode (see Figure 7-1).

FIGURE 7-1: PROGRAMMING EXECUTIVE SERIAL TIMING



Since a 2-wire SPI interface is used, and data transmissions are bidirectional, a simple protocol is used to control the direction of PGD. When the programmer completes a command transmission, it releases the PGD line and allows the programming executive to drive this line high. The programming executive keeps the PGD line high to indicate that it is processing the command.

After the programming executive has processed the command, it brings PGD low for 15 μsec to indicate to the programmer that the response is available to be

TABLE 8-1: PROGRAMMING EXECUTIVE COMMAND SET

Opcode	Mnemonic	Length (16-bit words)	Time Out	Description
0x0	SCHECK	1	1 ms	Sanity check.
0x1	READD	4	1 ms/row	Read N 16-bit words of data EEPROM, Configuration registers or device ID starting from specified address.
0x2	READP	4	1 ms/row	Read N 24-bit instruction words of code memory starting from specified address.
0x3	Reserved	N/A	N/A	This command is reserved. It will return a NACK.
0x4	PROGD(2)	19	5 ms	Program one row of data EEPROM at the specified address, then verify.
0x5	PROGP(1)	51	5 ms	Program one row of code memory at the specified address, then verify.
0x6	PROGC	4	5 ms	Write byte or 16-bit word to specified Configuration register.
0x7	ERASEB	2	5 ms	Bulk Erase (entire code memory or data EEPROM), or erase by segment.
0x8	ERASED(2)	3	5 ms/row	Erase rows of data EEPROM from specified address.
0x9	ERASEP(1)	3	5 ms/row	Erase rows of code memory from specified address.
0xA	QBLANK	3	300 ms	Query if the code memory and data EEPROM are blank.
0xB	QVER	1	1 ms	Query the programming executive software version.

Note 1: One row of code memory consists of (32) 24-bit words. Refer to Table 5-2 for device-specific information.
2: One row of data EEPROM consists of (16) 16-bit words. Refer to Table 5-3 for device-specific information.

8.5.7 ERASEB COMMAND

15 — 12	11 — 2	0
Opcode	Length	
Reserved		MS

Field	Description
Opcode	0x7
Length	0x2
Reserved	0x0
MS	Select memory to erase: 0x0 = All Code in General Segment 0x1 = All Data EEPROM in General Segment 0x2 = All Code and Data EEPROM in General Segment, interrupt vectors and FGS Configuration register 0x3 = Full Chip Erase 0x4 = All Code and Data EEPROM in Boot, Secure and General Segments, and FBS, FSS and FGS Configuration registers 0x5 = All Code and Data EEPROM in Secure and General Segments, and FSS and FGS Configuration registers 0x6 = All Data EEPROM in Boot Segment 0x7 = All Data EEPROM in Secure Segment

The ERASEB command performs a Bulk Erase. The MS field selects the memory to be bulk erased, with options for erasing Code and/or Data EEPROM in individual memory segments.

When Full Chip Erase is selected, the following memory regions are erased:

- All code memory (even if code-protected)
- All data EEPROM
- All code-protect Configuration registers

Only the executive code memory, Unit ID, device ID and Configuration registers that are not code-protected remain intact after a Chip Erase.

Expected Response (2 words):
0x1700
0x0002

Note:	A Full Chip Erase cannot be performed in low-voltage programming systems (VDD less than 4.5 volts). ERASED and ERASEP must be used to erase code memory, executive memory and data memory. Alternatively, individual Segment Erase operations may be performed.

8.5.8 ERASED COMMAND

15 — 12	11 — 8	7 — 0
Opcode	Length	
Num_Rows	Addr_MSB	
Addr_LS		

Field	Description
Opcode	0x8
Length	0x3
Num_Rows	Number of rows to erase (max of 128)
Addr_MSB	MSB of 24-bit base address
Addr_LS	LS 16 bits of 24-bit base address

The ERASED command erases the specified number of rows of data EEPROM from the specified base address. The specified base address must be a multiple of 0x20. Since the data EEPROM is mapped to program space, a 24-bit base address must be specified.

After the erase is performed, all targeted bytes of data EEPROM will contain 0xFF.

Expected Response (2 words):
0x1800
0x0002

Note:	The ERASED command cannot be used to erase the Configuration registers or device ID. Code-protect Configuration registers can only be erased with the ERASEB command, while the device ID is read-only.

9.2.3 QE_Code FIELD

The QE_Code is a byte in the first word of the response. This byte is used to return data for query commands, and error codes for all other commands.

When the programming executive processes one of the two query commands (QBLANK or QVER), the returned opcode is always PASS and the QE_Code holds the query response data. The format of the QE_Code for both queries is shown in Table 9-3.

TABLE 9-3: QE_Code FOR QUERIES

Query	QE_Code
QBLANK	0x0F = Code memory and data EEPROM are NOT blank 0xF0 = Code memory and data EEPROM are blank
QVER	0xMN, where programming executive software version = M.N (i.e., 0x32 means software version 3.2)

When the programming executive processes any command other than a Query, the QE_Code represents an error code. Supported error codes are shown in Table 9-4. If a command is successfully processed, the returned QE_Code is set to 0x0, which indicates that there was no error in the command processing. If the verify of the programming for the PROGD, PROGP or PROGC command fails, the QE_Code is set to 0x1. For all other programming executive errors, the QE_Code is 0x2.

TABLE 9-4: QE_Code FOR NON-QUERY COMMANDS

QE_Code	Description
0x0	No error
0x1	Verify failed
0x2	Other error

9.2.4 RESPONSE LENGTH

The response length indicates the length of the programming executive's response in 16-bit words. This field includes the 2 words of the response header.

With the exception of the response for the READD and READP commands, the length of each response is only 2 words.

The response to the READD command is N + 2 words, where N is the number of words specified in the READD command.

The response to the READP command uses the packed instruction word format described in **Section 8.3 "Packed Data Format"**. When reading an odd number of program memory words (N odd), the response to the READP command is (3 • (N + 1)/2 + 2) words. When reading an even number of program memory words (N even), the response to the READP command is (3 • N/2 + 2) words.

11.2.2 REGOUT SERIAL INSTRUCTION EXECUTION

The REGOUT control code allows for data to be extracted from the device in ICSP mode. It is used to clock the contents of the VISI register out of the device over the PGD pin. Once the REGOUT control code is received, eight clock cycles are required to process the command. During this time, the CPU is held idle. After these eight cycles, an additional 16 cycles are required to clock the data out (see Figure 11-3).

The REGOUT instruction is unique because the PGD pin is an input when the control code is transmitted to the device. However, once the control code is processed, the PGD pin becomes an output as the VISI register is shifted out. After the contents of the VISI are shifted out, PGD becomes an input again as the state machine holds the CPU idle until the next 4-bit control code is shifted in.

Note:	Once the contents of VISI are shifted out, the dsPIC® DSC device maintains PGD as an output until the first rising edge of the next clock is received.

FIGURE 11-1: PROGRAM ENTRY AFTER RESET

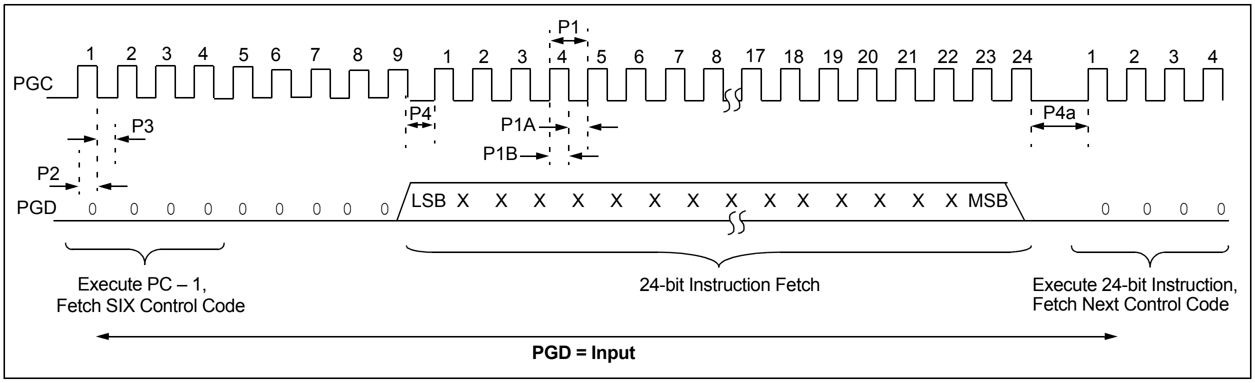


FIGURE 11-2: SIX SERIAL EXECUTION

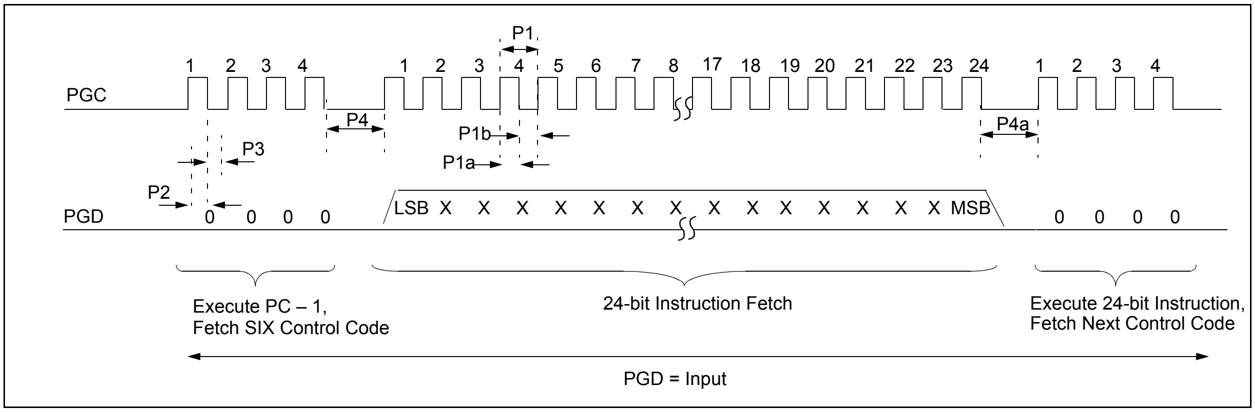


FIGURE 11-3: REGOUT SERIAL EXECUTION

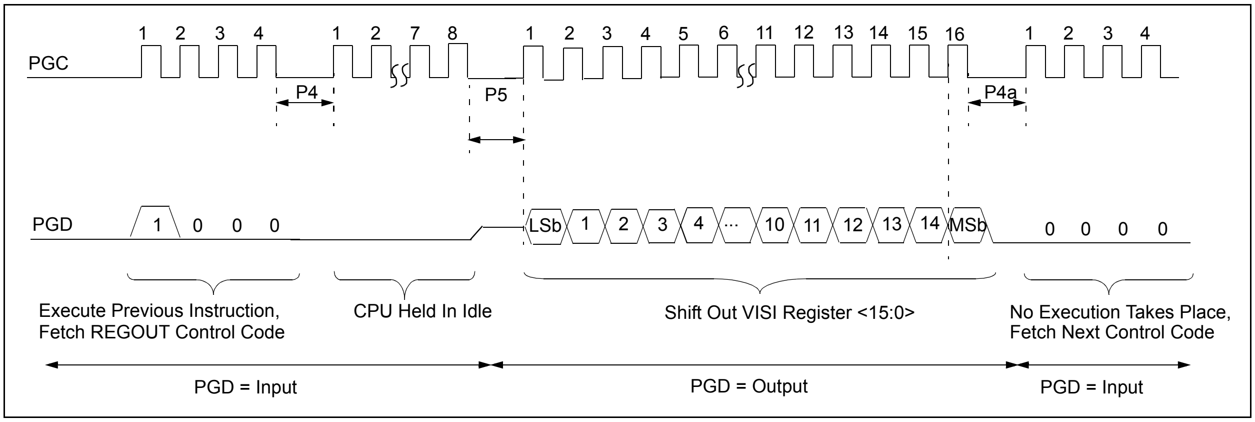


Table 11-4 shows the ICSP programming process for bulk-erasing program memory. This process includes the ICSP command code, which must be transmitted (for each instruction) to the Least Significant bit first using the PGC and PGD pins (see Figure 11-2).

If an individual Segment Erase operation is required, the NVMCON value must be replaced by the value for the corresponding Segment Erase operation.

Note:	Program memory must be erased before writing any data to program memory.

TABLE 11-4: SERIAL INSTRUCTION EXECUTION FOR BULK ERASING PROGRAM MEMORY (ONLY IN NORMAL-VOLTAGE SYSTEMS)

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000 0000 0000	040100 040100 000000	GOTO 0x100 GOTO 0x100 NOP
Step 2: Set NVMCON to program the FBS Configuration register.(1)		
0000 0000	24008A 883B0A	MOV #0x4008, W10 MOV W10, NVMCON
Step 3: Initialize the TBLPAG and write pointer (W7) for TBLWT instruction for Configuration register.(1)		

0000
0000
0000
	200F80
	880190
	200067
		MOV #0xF8, W0
		MOV W0, TBLPAG
		MOV #0x6, W7

Step 4: Load the Configuration Register data to W6.(1)		
0000 0000	EB0300 000000	CLR W6 NOP
Step 5: Load the Configuration Register write latch. Advance W7 to point to next Configuration register.(1)		
0000	BB1B86	TBLWTL W6, [W7++]
Step 6: Unlock the NVMCON for programming the Configuration register.(1)		

0000
0000
0000
0000
	200558
	200AA9
	883B38
	883B39
		MOV #0x55, W8
		MOV #0xAA, W9
		MOV W8, NVMKEY
		MOV W9, NVMKEY

Step 7: Initiate the programming cycle.(1)		
0000 0000 0000 — 0000 0000 0000 0000 0000	A8E761 000000 000000 — 000000 000000 A9E761 000000 000000	BSET NVMCON, #WR NOP NOP Externally time 2 ms NOP NOP BCLR NVMCON, #WR NOP NOP
Step 8: Repeat steps 5-7 one time to program 0x0000 to RESERVED2 Configuration register.(1)		
Step 9: Set the NVMCON to erase all Program Memory.		
00000 0000	2407FA 883B0A	MOV #0x407F, W10 MOV W10, NVMCON
Step 10: Unlock the NVMCON for programming.		

Note 1: Steps 2-8 are only required for the dsPIC30F5011/5013 devices. These steps may be skipped for all other devices in the dsPIC30F family.

TABLE 11-5: SERIAL INSTRUCTION EXECUTION FOR ERASING PROGRAM MEMORY (EITHER IN LOW-VOLTAGE OR NORMAL-VOLTAGE SYSTEMS) (CONTINUED)

Command (Binary)	Data (Hexadecimal)	Description
Step 6: Update the row address stored in NVMADRU:NVMADR. When W6 rolls over to 0x0, NVMADRU must be incremented.		

0000
0000
0000
0000
	430307
	AF0042
	EC2764
	883B16
		`ADD W6, W7, W6`
		`BTSC SR, #C`
		`INC NVMADRU`
		`MOV W6, NVMADR`

Step 7: Reset device internal PC.		
0000 0000	040100 000000	`GOTO 0x100` `NOP`
Step 8: Repeat Steps 3-7 until all rows of code memory are erased.		
Step 9: Initialize NVMADR and NVMADRU to erase executive memory and initialize W7 for row address updates.		

0000
0000
0000
0000
0000
	EB0300
	883B16
	200807
	883B27
	200407
		`CLR W6`
		`MOV W6, NVMADR`
		`MOV #0x80, W7`
		`MOV W7, NVMADRU`
		`MOV #0x40, W7`

Step 10: Set NVMCON to erase 1 row of executive memory.		
0000 0000	24071A 883B0A	`MOV #0x4071, W10` `MOV W10, NVMCON`
Step 11: Unlock the NVMCON to erase 1 row of executive memory.		

0000
0000
0000
0000
	200558
	883B38
	200AA9
	883B39
		`MOV #0x55, W8`
		`MOV W8, NVMKEY`
		`MOV #0xAA, W9`
		`MOV W9, NVMKEY`

Step 12: Initiate the erase cycle.		

0000
0000
0000
—
0000
0000
0000
0000
0000
	A8E761
	000000
	000000
	—
	000000
	000000
	A9E761
	000000
	000000
		`BSET NVMCON, #WR`
		`NOP`
		`NOP`
		`Externally time 'P13a' ms` (see **Section 13.0 "AC/DC Characteristics and Timing Requirements"**)
		`NOP`
		`NOP`
		`BCLR NVMCON, #WR`
		`NOP`
		`NOP`

Step 13: Update the row address stored in NVMADR.		
0000 0000	430307 883B16	`ADD W6, W7, W6` `MOV W6, NVMADR`
Step 14: Reset device internal PC.		
0000 0000	040100 000000	`GOTO 0x100` `NOP`
Step 15: Repeat Steps 10-14 until all 24 rows of executive memory are erased.		
Step 16: Initialize NVMADR and NVMADRU to erase data memory and initialize W7 for row address updates.		

0000
0000
0000
0000
0000
	2XXXX6
	883B16
	2007F6
	883B16
	200207
		MOV #<lower 16-bits of starting Data EEPROM address>, W6
		`MOV W6, NVMADR`
		`MOV #0x7F, W6`
		`MOV W6, NVMADRU`
		`MOV #0x20, W7`

Step 17: Set NVMCON to erase 1 row of data memory.		
0000 0000	24075A 883B0A	`MOV #0x4075, W10` `MOV W10, NVMCON`

TABLE 11-7: SERIAL INSTRUCTION EXECUTION FOR WRITING CONFIGURATION REGISTERS (CONTINUED)

Command (Binary)	Data (Hexadecimal)	Description
Step 6: Write the Configuration register data to the write latch and increment the write pointer.		
0000 0000 0000	BB1B96 000000 000000	TBLWTL W6, [W7++] NOP NOP
Step 7: Unlock the NVMCON for programming.		

0000
0000
0000
0000
	200558
	883B38
	200AA9
	883B39
		MOV #0x55, W8
		MOV W8, NVMKEY
		MOV #0xAA, W9
		MOV W9, NVMKEY

Step 8: Initiate the write cycle.		
0000 0000 0000 — 0000 0000 0000 0000 0000	A8E761 000000 000000 — 000000 000000 A9E761 000000 000000	BSET NVMCON, #WR NOP NOP Externally time 'P12a' ms (see **Section 13.0 "AC/DC Characteristics and Timing Requirements"**) NOP NOP BCLR NVMCON, #WR NOP NOP
Step 9: Reset device internal PC.		
0000 0000	040100 000000	GOTO 0x100 NOP
Step 10: Repeat steps 3-9 until all 7 Configuration registers are cleared.		

TABLE 11-8: SERIAL INSTRUCTION EXECUTION FOR WRITING CODE MEMORY (CONTINUED)

Command (Binary)	Data (Hexadecimal)	Description
Step 5: Set the read pointer (W6) and load the (next set of) write latches.		
0000	EB0300	CLR W6
0000	000000	NOP
0000	BB0BB6	TBLWTL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP
0000	BBDBB6	TBLWTH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BBEBB6	TBLWTH.B [W6++], [++W7]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB0BB6	TBLWTL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP
0000	BBDBB6	TBLWTH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BBEBB6	TBLWTH.B [W6++], [++W7]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
Step 6: Repeat steps 4-5 eight times to load the write latches for 32 instructions.		
Step 7: Unlock the NVMCON for writing.		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
Step 8: Initiate the write cycle.		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P12a' ms (see **Section 13.0 "AC/DC Characteristics and Timing Requirements"**)
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
Step 9: Reset device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
Step 10: Repeat steps 2-9 until all code memory is programmed.		

11.9 Writing Data EEPROM

The procedure for writing data EEPROM is very similar to the procedure for writing code memory, except that fewer words are programmed in each operation. When writing data EEPROM, one row of data EEPROM is programmed at a time. Each row consists of sixteen 16-bit data words. Since fewer words are programmed during each operation, only working registers W0:W3 are used as temporary holding registers for the data to be programmed.

Table 11-9 shows the ICSP programming details for writing data EEPROM. Note that a different NVMCON value is required to write to data EEPROM, and that the TBLPAG register is hard-coded to 0x7F (the upper byte address of all locations of data EEPROM).

TABLE 11-9: SERIAL INSTRUCTION EXECUTION FOR WRITING DATA EEPROM

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
Step 2: Set the NVMCON to write 16 data words.		
0000	24005A	MOV #0x4005, W10
0000	883B0A	MOV W10, NVMCON
Step 3: Initialize the write pointer (W7) for TBLWT instruction.		
0000	2007F0	MOV #0x7F, W0
0000	880190	MOV W0, TBLPAG
0000	2xxxx7	MOV #<DestinationAddress15:0>, W7
Step 4: Load W0:W3 with the next 4 data words to program.		
0000	2xxxx0	MOV #<WORD0>, W0
0000	2xxxx1	MOV #<WORD1>, W1
0000	2xxxx2	MOV #<WORD2>, W2
0000	2xxxx3	MOV #<WORD3>, W3
Step 5: Set the read pointer (W6) and load the (next set of) write latches.		
0000	EB0300	CLR W6
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
Step 6: Repeat steps 4-5 four times to load the write latches for 16 data words.		

TABLE 11-9: SERIAL INSTRUCTION EXECUTION FOR WRITING DATA EEPROM (CONTINUED)

Command (Binary)	Data (Hexadecimal)	Description
Step 7: Unlock the NVMCON for writing.		

0000
0000
0000
0000
	200558
	883B38
	200AA9
	883B39
		`MOV #0x55, W8`
		`MOV W8, NVMKEY`
		`MOV #0xAA, W9`
		`MOV W9, NVMKEY`

Step 8: Initiate the write cycle.		

0000
0000
0000
—
 	
0000
0000
0000
0000
0000
	A8E761
	000000
	000000
	—
	
	000000
	000000
	A9E761
	000000
	000000
		`BSET NVMCON, #WR`
		`NOP`
		`NOP`
		`Externally time 'P12a' ms` (see **Section 13.0 "AC/DC Characteristics and Timing Requirements"**)
		`NOP`
		`NOP`
		`BCLR NVMCON, #WR`
		`NOP`
		`NOP`

Step 9: Reset device internal PC.		
0000 0000	040100 000000	`GOTO 0x100` `NOP`
Step 10: Repeat steps 2-9 until all data memory is programmed.		

11.10 Reading Code Memory

Reading from code memory is performed by executing a series of TBLRD instructions and clocking out the data using the REGOUT command. To ensure efficient execution and facilitate verification on the programmer, four instruction words are read from the device at a time.

Table 11-10 shows the ICSP programming details for reading code memory. In Step 1, the Reset vector is exited. In Step 2, the 24-bit starting source address for reading is loaded into the TBLPAG and W6 registers. The upper byte of the starting source address is stored to TBLPAG, while the lower 16 bits of the source address are stored to W6.

To minimize the reading time, the packed instruction word format that was utilized for writing is also used for reading (see Figure 11-5). In Step 3, the write pointer W7 is initialized, and four instruction words are read from code memory and stored to working registers W0:W5. In Step 4, the four instruction words are clocked out of the device from the VISI register using the REGOUT command. In Step 5, the internal PC is reset to 0x100, as a precautionary measure, to prevent the PC from incrementing into unimplemented memory when large devices are being read. Lastly, in Step 6, Steps 3-5 are repeated until the desired amount of code memory is read.

TABLE 11-10: SERIAL INSTRUCTION EXECUTION FOR READING CODE MEMORY

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
Step 2: Initialize TBLPAG and the read pointer (W6) for TBLRD instruction.		
0000	200xx0	MOV #<SourceAddress23:16>, W0
0000	880190	MOV W0, TBLPAG
0000	2xxxx6	MOV #<SourceAddress15:0>, W6
Step 3: Initialize the write pointer (W7) and store the next four locations of code memory to W0:W5.		
0000	EB0380	CLR W7
0000	000000	NOP
0000	BA1B96	TBLRDL [W6], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBB6	TBLRDH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBD6	TBLRDH.B [++W6], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1B96	TBLRDL [W6], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBB6	TBLRDH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBD6	TBLRDH.B [++W6], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA0BB6	TBLRDL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP

12.2 Programming Verification

After the programming executive has been programmed to executive memory using ICSP, it must be verified. Verification is performed by reading out the contents of executive memory and comparing it with the image of the programming executive stored in the programmer.

Reading the contents of executive memory can be performed using the same technique described in **Section 11.10 "Reading Code Memory"**. A procedure for reading executive memory is shown in Table 12-2. Note that in Step 2, the TBLPAG register is set to 0x80 such that executive memory may be read.

TABLE 12-2: READING EXECUTIVE MEMORY

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
Step 2: Initialize TBLPAG and the read pointer (W6) for TBLRD instruction.		
0000	200800	MOV #0x80, W0
0000	880190	MOV W0, TBLPAG
0000	EB0300	CLR W6
Step 3: Initialize the write pointer (W7), and store the next four locations of executive memory to W0:W5.		
0000	EB0380	CLR W7
0000	000000	NOP
0000	BA1B96	TBLRDL [W6], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBB6	TBLRDH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBD6	TBLRDH.B [++W6], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1B96	TBLRDL [W6], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBB6	TBLRDH.B [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BADBD6	TBLRDH.B [++W6], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BA1BB6	TBLRDL [W6++], [W7]
0000	000000	NOP
0000	000000	NOP

TABLE 12-2: READING EXECUTIVE MEMORY (CONTINUED)

Command (Binary)	Data (Hexadecimal)	Description
Step 4: Output W0:W5 using the VISI register and REGOUT command.		
0000	883C20	MOV W0, VISI
0000	000000	NOP
0001	—	Clock out contents of VISI register
0000	883C21	MOV W1, VISI
0000	000000	NOP
0001	—	Clock out contents of VISI register
0000	883C22	MOV W2, VISI
0000	000000	NOP
0001	—	Clock out contents of VISI register
0000	883C23	MOV W3, VISI
0000	000000	NOP
0001	—	Clock out contents of VISI register
0000	883C24	MOV W4, VISI
0000	000000	NOP
0001	—	Clock out contents of VISI register
0000	883C25	MOV W5, VISI
0000	000000	NOP
0001	—	Clock out contents of VISI register
Step 5: Reset the device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
Step 6: Repeat Steps 3-5 until all 736 instruction words of executive memory are read.		